

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Amended) A [semiconductor device] ferroelectric liquid crystal display device having  
a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said [semiconductor device]  
CMOS circuit comprising:  
each gate electrode of said n-channel TFT and said p-channel TFT [has] having a first  
conductive layer being in contact with a gate insulating film, and a second conductive layer being  
in contact with both said first conductive layer and said gate insulating film;  
a semiconductor layer of said n-channel TFT comprising a first channel formation region,  
a first impurity region being in contact with said first channel formation region, and a second  
impurity region being in contact with said first impurity region; and  
a semiconductor layer of said p-channel TFT comprising a second channel formation region  
and a third impurity region being in contact with said second channel formation region,  
wherein said first impurity region of said n-channel TFT is disposed so as to [completely]  
partially [overlap[s]] with [said second conductive layer] a portion of said second conductive layer  
which is in contact with said gate insulating film;  
wherein said third impurity region of said p-channel TFT is disposed so as to partially  
[overlap[s]] with [said second conductive layer] another portion of said second conductive layer  
which is in contact with said gate insulating film.

Please add following claims.

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A2  
p, 7  
# 2. A ferroelectric liquid crystal display device according to claim 1, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).~~4~~

#-3. A ferroelectric liquid crystal display device according to claim 1, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers.~~4~~

#-4. A ferroelectric liquid crystal display device according to claim 1, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).~~4~~

Sub C2  
#-5. A ferroelectric liquid crystal display device according to claim 1, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.~~4~~

Sub B2  
#-6. A ferroelectric liquid crystal display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

5 each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

B2  
a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

10 wherein said first impurity region of said n-channel TFT is disposed so as to partially  
12 [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

15 wherein said second impurity region of said n-channel TFT is disposed so as not to  
[overlaps] with said second conductive <sup>layer</sup> [film];

17 wherein said third impurity region of said p-channel TFT is disposed so as to partially  
[overlaps] with <sup>a</sup> [said] portion which said second conductive layer is in contact with said gate insulating film. 4

Cont.  
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7. A ferroelectric liquid crystal display device according to claim 6, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). 4

112 1st 8. A ferroelectric liquid crystal display device according to claim 6, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers. -5

9. A ferroelectric liquid crystal display device according to claim 6, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Sub C4  
10. A ferroelectric liquid crystal display device according to claim 6, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

Sub B3  
11. A ferroelectric liquid crystal display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

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a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region;

wherein said first impurity region is disposed so as to partially overlaps with said first gate electrode, and

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said p-channel TFT comprising:

a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film, said second semiconductor layer comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

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wherein said third impurity region is disposed so as to partially overlaps with said second gate electrode.

Sub Cb →  
12. A ferroelectric liquid crystal display device according to claim 11, wherein said first and second gate<sup>electrodes</sup> comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

13. A ferroelectric liquid crystal display device according to claim 11, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

p. 57, fig. 15D  
14. A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

wherein said first impurity region of said n-channel TFT is disposed so as to partially [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

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wherein said third impurity region of said p-channel TFT is disposed so as to partially  
<sup>a</sup>  
[overlaps] with [said] portion which said second conductive layer is in contact with said gate insulating  
film. ¶

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F1

15. A goggle type display device according to claim 14, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). ¶

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16. A goggle type display device according to claim 14, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers. ¶

A2  
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17. A goggle type display device according to claim 14, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). ¶

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18. A goggle type display device according to claim 14, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region. ¶

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19. A goggle type display device having a CMOS circuit comprising an n-channel TFT and a p-channel TFT, said CMOS circuit comprising:

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each gate electrode of said n-channel TFT and said p-channel TFT having a first conductive layer being in contact with a gate insulating film, and a second conductive layer being in contact with both said first conductive layer and said gate insulating film;

a semiconductor layer of said n-channel TFT comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region; and

10 a semiconductor layer of said p-channel TFT comprising a second channel formation region and a third impurity region being in contact with said second channel formation region,

Ad  
wherein said first impurity region of said n-channel TFT is disposed so as to partially [overlaps] with a portion which said second conductive layer is in contact with said gate insulating film;

15 Cnt. [overlaps] with said second conductive <sup>layer</sup> [film];

17 wherein said third impurity region of said p-channel TFT is disposed so as to partially [overlaps] with <sup>a</sup> [said] portion which said second conductive layer is in contact with said gate insulating film. 4

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20. A goggle type display device according to claim 19, wherein said first conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo). 4

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21. A goggle type display device according to claim 19, wherein each of said first conductive layers of said n-channel TFT and said p-channel TFT comprises [a single layer] or a plurality of layers.

22. A goggle type display device according to claim 19, wherein said second conductive layers of said n-channel TFT and said p-channel TFT comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Sub C10  
23. A goggle type display device according to claim 19, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

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24. A goggle type display device having an n-channel TFT and a p-channel TFT over a substrate,

said n-channel TFT comprising:

5 a first gate electrode formed adjacent to a first semiconductor layer with a first gate insulating film interposed therebetween, said first semiconductor layer comprising a first channel formation region, a first impurity region being in contact with said first channel formation region, and a second impurity region being in contact with said first impurity region;

wherein said first impurity region is disposed so as to partially [overlaps] with said first gate electrode, and

10 said p-channel TFT comprising:



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15 a second gate electrode formed adjacent to a second semiconductor layer with a second gate insulating film, said second semiconductor layer comprising a second channel formation region and a third impurity region being in contact with said second channel formation region, wherein said third impurity region is disposed so as to partially overlaps with said second gate electrode.

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25. A goggle type display device according to claim 24, wherein said first and second gate<sup>electrodes</sup> comprise a material selected from the group consisting of titanium (Ti), tantalum (Ta), tungsten (W), and molybdenum (Mo).

Cont.  
26. A goggle type display device according to claim 24, wherein said first impurity region is a LDD region, said second impurity region is a source or a drain region, and said third impurity region is the source or the drain region.

### REMARKS

#### I. Title

In the Office Action, the Examiner objects to the title of the invention as not being descriptive. Accordingly, Applicants are amending the title to recite -- Ferroelectric Liquid Crystal and Goggle Type Display Devices -- , which is consistent with the claims herein. Therefore, it is requested that this rejection be withdrawn.